2102-F,I,N • 2102-1-F,I,N • 2102-2-F,I,N

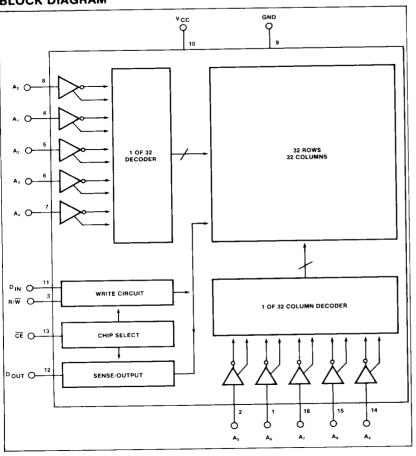
## **DESCRIPTION**

The 2102, 2102-1 and 2102-2 are static random access read/write memories fabricated with low threshold n-channel silicon gate technology.

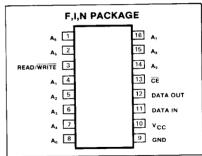
## **FEATURES**

- Fully static
- Require no clocks
- Completely DTL/TTL compatible
- Single 5V power supply
- Three-state output for OR-tie capability

## **BLOCK DIAGRAM**



## PIN CONFIGURATION



## ABSOLUTE MAXIMUM RATINGS1

	PARAMETER	RATING	UNIT
Tstg PD	Temperature range Storage Power dissipation <sup>2</sup> N package F package I package All input, output and supply voltages with respect to ground	-65 to 150 640 1 1 -0.5 to 7	°C mW W V

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# DC ELECTRICAL CHARACTERISTICS $T_A = 0$ °C to 70°C, $V_{CC} = 5V \pm 5\%$ unless otherwise specified.

	PARAMETER	TEST CONDITIONS		Ī			
	FANAMETER	TEST CONDITIONS	Min	Typ1	0.65 Vcc	UNIT	
VIL VIH	Input voltage Low High		-0.5 2.2			٧	
V <sub>OL</sub> V <sub>OH</sub>	Output voltage Low High	I <sub>OL</sub> = 1.9mA I <sub>OH</sub> = -100µA	2.2		0.45	V	
ILI	Input load current (All input pins)	V <sub>IN</sub> = 0 to 5.25V		1	10	μА	
ILOH ILOL	Leakage current	CE = 2.2V V <sub>OUT</sub> = 4.0V V <sub>OUT</sub> = 0.45V			10 -100	μА	
lcc1 lcc2	Supply current	All inputs = 5.25V, Data out open $T_A = 25^{\circ}C$ $T_A = 0^{\circ}C$		30	60 70	mA	

# AC ELECTRICAL CHARACTERISTICS $T_A = 0$ °C to 70°C, $V_{CC} = 5V \pm 5\%$ unless otherwise specified.

	DADAMETED	TO FROM  Output Chip enable		2102		2102-1		2102-2					
	PARAMETER		FROM	<b>Min</b> 1,000	377	1,000 500	500	<u> </u>	500 350	<b>Min</b> 650	Тур	650 400	ns ns ns
trc ta tco	READ CYCLE Read cycle Access time		Chip enable										
tон1 tон2	Previous data valid with respect to Address Chip enable			50 0			50 0			50 0			ns
twc twp twn	WRITE CYCLE Write cycle Write pulse width Write recovery time			1,000 750 50			500 300 50			650 400 50			ns ns ns
taw tow toh	Setup and hold time Setup time Setup time Hold time	Write Rise of R/W Change of data in	Address Data in Rise of R/W	200 800 100			150 330 100			200 450 100			ns
tcw	Setup time	Write	Chip enable	900		1	400	,		550			

#### NOTES

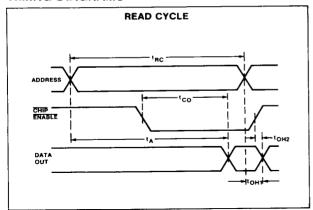
- 1. Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only and functional operation of the device of these or any other condition above those indicated in the operation of the device of these or any other condition above those indicated in the operation sections of this specification is not implied.
- 2. For operating at elevated temperatures the device must be derated based on a +150°C maximum junction temperature and a thermal resistance of 150°C/W junction to ambient ("B" package)
- All inputs protected against static charge.
- Parameter valid over operating temperature range unless otherwise specified.
- 5. All voltage measurements are referenced to ground.
- Manufacturer reserves the right to make design and process changes and improvements.
   Typical values are at +25°C and typical supply voltages.

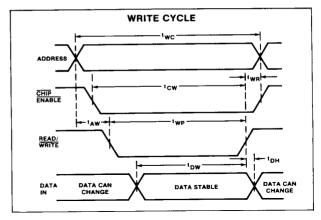
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## **TIMING DIAGRAMS**





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